

Product data sheet

1. General description

Planar passivated high commutation three quadrant triac in a TO263 (D2PAK) plastic package intended for use in circuits where high static and dynamic dV/dt and high dl/dt can occur. This "series C" triac will commutate the full rated RMS current at the maximum rated junction temperature without the aid of a snubber.

2. Features and benefits

- 3Q technology for improved noise immunity
- High commutation capability with maximum false trigger immunity
- High immunity to false turn-on by dV/dt
- High voltage capability
- · Planar passivated for voltage ruggedness and reliability
- Surface mountable package
- Triggering in three quadrants only

3. Applications

- Electronic thermostats (heating and cooling)
- · High power motor controls e.g. washing machines and vacuum cleaners
- · Rectifier-fed DC inductive loads e.g. DC motors and solenoids

4. Quick reference data

Table 1. Q	uick reference data						
Symbol	Parameter	Conditions	Values			Unit	
Absolute	maximum rating						
V_{DRM}	repetitive peak off-state voltage			6	00		V
$I_{\mathrm{T}(\mathrm{RMS})}$	RMS on-state current	full sine wave; T _{mb} ≤ 101 °C <u>Fig. 1; Fig. 2; Fig. 3</u>	16			A	
I _{TSM}	non-repetitive peak on- state current	full sine wave; T _{j(init)} = 25 °C; t _p = 20 ms <u>Fig. 4; Fig. 5</u>	140			A	
		full sine wave; $T_{j(init)}$ = 25 °C; t_p = 16.7 ms		1	50		А
T _j	junction temperature		125			°C	
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Static ch	aracteristics						
I _{GT}	gate trigger current	V_{D} = 12 V; I _T = 0.1 A; T2+ G+; T _j = 25 °C; <u>Fig. 7</u>		2	-	35	mA
		$V_{\rm D}$ = 12 V; I _T = 0.1 A; T2+ G-; T _i = 25 °C; <u>Fig. 7</u>		2	-	35	mA

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
		$V_{D} = 12 \text{ V}; \text{ I}_{T} = 0.1 \text{ A}; \text{ T2- G-};$ $T_{j} = 25 \text{ °C}; \text{ Fig. 7}$	2	-	35	mA
I _H	holding current	V _D = 12 V; T _j = 25 °C; <u>Fig. 9</u>	-	-	35	mA
V _T	on-state voltage	I _T = 18 A; T _j = 25 °C; <u>Fig. 10</u>	-	1.3	1.5	V
Dynamic	characteristics					
dV _D /dt	rate of rise of off-state voltage	$V_{DM} = 402 \text{ V}; \text{ T}_{\text{j}} = 125 \text{ °C}; (V_{DM} = 67\% \text{ of } V_{DRM});$ exponential waveform; gate open circuit	500	-	-	V/µs
dl _{com} /dt	rate of change of commutating current	$V_D = 400 \text{ V}; \text{ T}_j = 125 \text{ °C}; \text{ I}_{T(RMS)} = 16 \text{ A};$ $dV_{com}/dt = 20 \text{ V}/\mu \text{s}; \text{ (snubberless condition); gate open circuit}$	15	-	-	A/ms

5. Pinning information

Table 2. P	Table 2. Pinning information								
Pin	Symbol	Description	Simplified outline	Graphic symbol					
1	T1	main terminal 1		NI					
2	T2	main terminal 2		T2-T1					
3	G	gate		`G sym051					
mb	Τ2	mounting base; main terminal 2							

6. Ordering information

Table 3. Ordering information								
Type number	Package Name	Orderable part number	Packing method	Small packing quantity	Package version	Package issue date		
BTA316B-600C	TO263	BTA316B-600C,118	Reel	800	TO263E	26-May-2017		

7. Marking

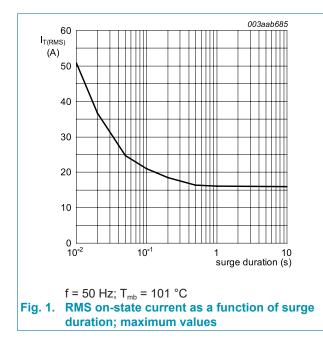
Table 4. Marking codes	
Type number	Marking codes
BTA316B-600C	BTA316B-600C

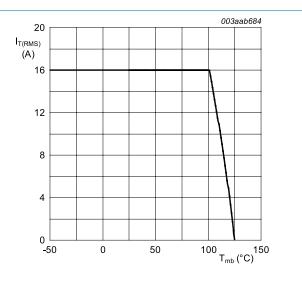
8. Limiting values

Table 5. Limiting values

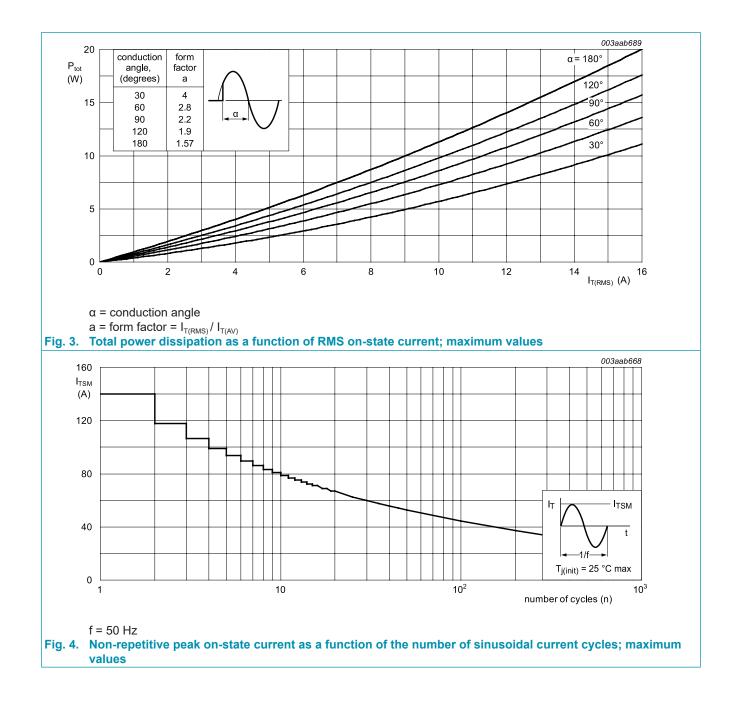
In accordance with the Absolute Maximum Rating System (IEC 60134).

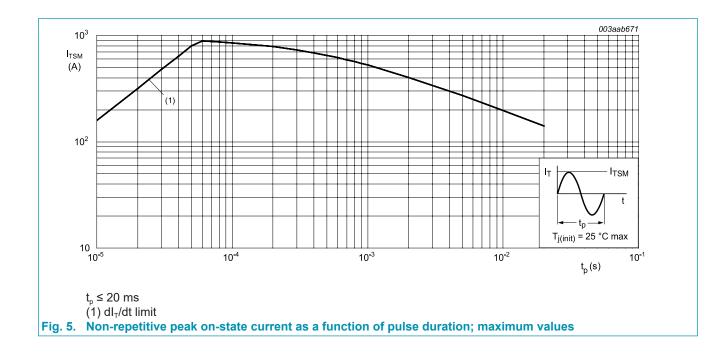
Symbol	Parameter	Conditions	Values	Unit
V_{DRM}	repetitive peak off-state voltage		600	V
I _{T(RMS)}	RMS on-state current	full sine wave; T _{mb} ≤ 101 °C <u>Fig 1</u> ; <u>Fig 2</u> ; <u>Fig 3</u>	16	A
I _{TSM}	non-repetitive peak on- state current	full sine wave; $T_{j(init)}$ = 25 °C; t_p = 20 ms Fig 4; Fig 5	140	A
		full sine wave; $T_{j(init)}$ = 25 °C; t_p = 16.7 ms	150	A
l ² t	I ² t for fusing	t _P = 10 ms; SIN	98	A ² s
dI _T /dt	rate of rise of on-state current	I _G = 70 mA	100	A/µs
I _{GM}	peak gate current		2	А
P_{GM}	peak gate power		5	W
$P_{G(AV)}$	average gate power	over any 20 ms period	0.5	W
T _{stg}	storage temperature		-40 to 150	°C
Tj	junction temperature		125	°C





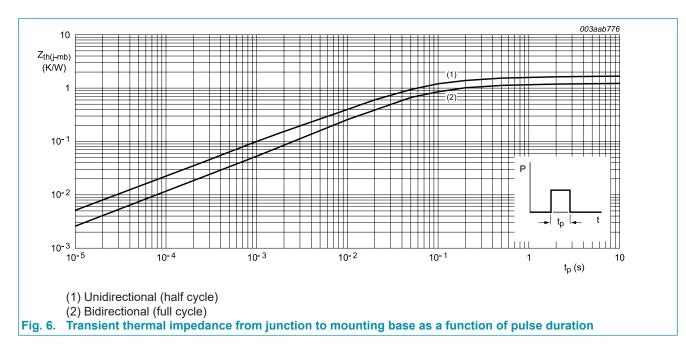






9. Thermal characteristics

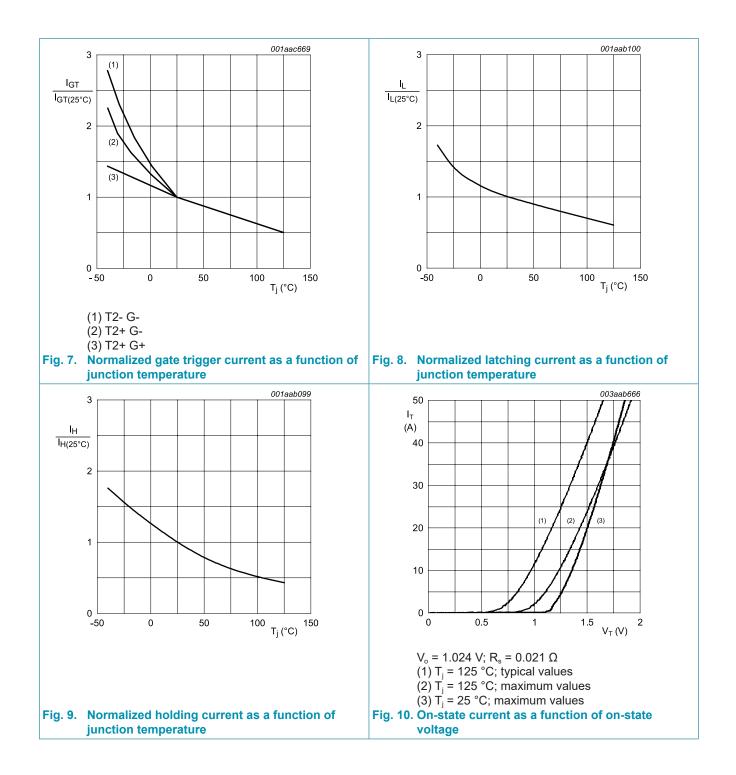
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Cymbol	i didifictei	oonations		IJP	Inax	Unit
$R_{\text{th(j-mb)}}$	thermal resistance	full cycle; <u>Fig 6</u>	-	-	1.2	K/W
	from junction to mounting base	half cycle; <u>Fig 6</u>	-	-	1.7	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient free air	printed circuit board mounted; minimum footprint	-	55	-	K/W

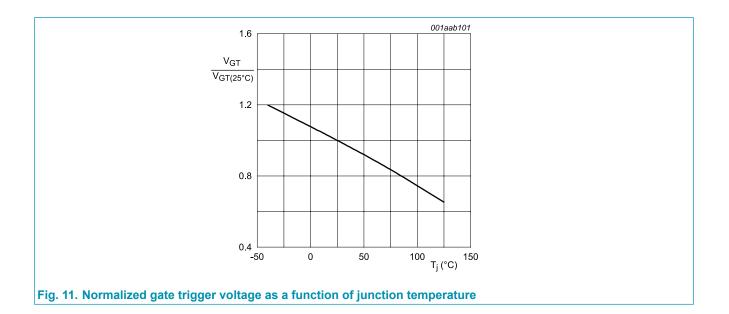


10. Characteristics

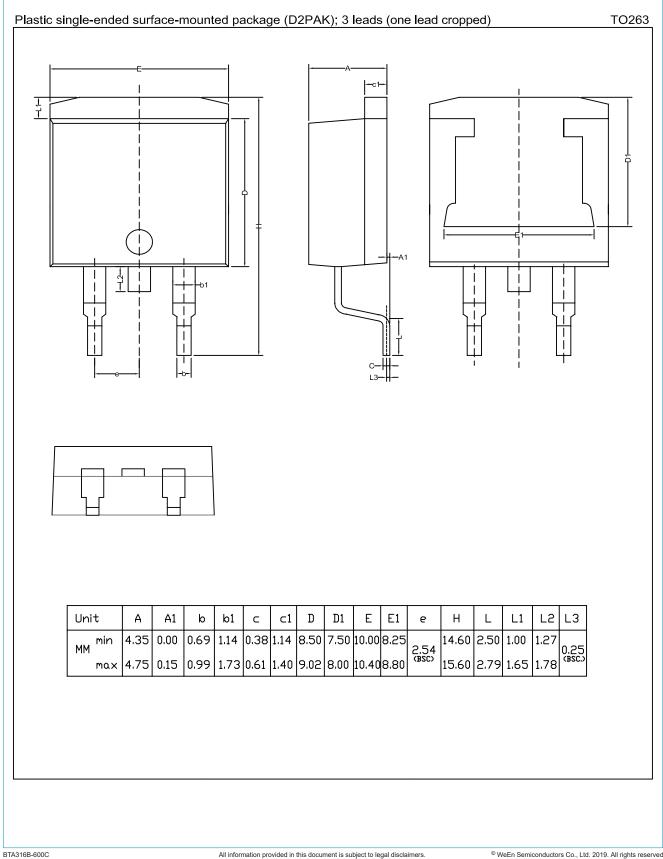
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	aracteristics	· · · · · · · · · · · · · · · · · · ·				_
I _{GT}	gate trigger current	$V_{D} = 12 \text{ V}; \text{ I}_{T} = 0.1 \text{ A}; \text{ T2+ G+};$ T _j = 25 °C; Fig. 7	2	-	35	mA
		$V_{\rm D}$ = 12 V; I _T = 0.1 A; T2+ G-; T _j = 25 °C; Fig. 7	2	-	35	mA
		$V_{\rm D}$ = 12 V; I _T = 0.1 A; T2- G-; T _j = 25 °C; Fig. 7	2	-	35	mA
I _L	latching current	$V_{\rm D}$ = 12 V; I _G = 0.1 A; T2+ G+; T _j = 25 °C; Fig. 8	-	-	50	mA
		V _D = 12 V; I _G = 0.1 A; T2+ G-; T _j = 25 °C; <u>Fig. 8</u>	-	-	60	mA
		V _D = 12 V; I _G = 0.1 A; T2- G-; T _j = 25 °C; <u>Fig. 8</u>	-	-	50	mA
I _H	holding current	V _D = 12 V; T _j = 25 °C; <u>Fig. 9</u>	-	-	35	mA
V _T	on-state voltage	I _T = 18 A; T _j = 25 °C; <u>Fig. 10</u>	-	1.3	1.5	V
V _{GT}	gate trigger voltage	$V_{D} = 12 \text{ V}; \text{ I}_{T} = 0.1 \text{ A}; \text{ T}_{j} = 25 \text{ °C};$ Fig. 11	-	0.8	1	V
		V _D = 400 V; I _T = 0.1 A; T _j = 125 °C; Fig. 11	0.25	0.4	-	V
I _D	off-state current	V _D = 600 V; T _j = 125 °C	-	0.1	0.5	mA
Dynamic	characteristics	· · · ·				
dV _D /dt	rate of rise of off-state voltage $V_{DM} = 402 \text{ V}; \text{ T}_{j} = 125 \text{ °C}; (V_{DM} = 67\% \text{ of } V_{DRM}); exponential waveform; gate open circuit$		500	-	-	V/µs
dl _{com} /dt	rate of change of commutating current	$V_D = 400 \text{ V}; \text{ T}_j = 125 \text{ °C}; \text{ I}_{T(RMS)} = 16 \text{ A};$ $dV_{com}/dt = 20 \text{ V}/\mu\text{s}; \text{ (snubberless condition); gate open circuit}$	15	-	-	A/ms

BTA316B-600C 3Q Hi-Com Triac





11. Package outline



BTA316B-600C 3Q Hi-Com Triac

12. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

- [2] The term 'short data sheet' is explained in section "Definitions".
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